

Zhang Zhou

List of Publications by Year in descending order

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12
papers

1,015
citations

840776

11
h-index

1199594

12
g-index

13
all docs

13
docs citations

13
times ranked

1588
citing authors

#	ARTICLE	IF	CITATIONS
1	Dimensional crossover in self-intercalated antiferromagnetic V_5S_8 nanoflakes. <i>Physical Review B</i> , 2022, 105, ...	3.2	6
2	Anomalous thickness dependence of Curie temperature in air-stable two-dimensional ferromagnetic 1T-CrTe ₂ grown by chemical vapor deposition. <i>Nature Communications</i> , 2021, 12, 809.	12.8	196
3	One-dimensional weak antilocalization effect in 1T ϵ^2 -MoTe ₂ nanowires grown by chemical vapor deposition. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 185701.	1.8	0
4	Atomically sharp interface enabled ultrahigh-speed non-volatile memory devices. <i>Nature Nanotechnology</i> , 2021, 16, 882-887.	31.5	105
5	Insulating SiO ₂ under Centimeter-Scale, Single-Crystal Graphene Enables Electronic-Device Fabrication. <i>Nano Letters</i> , 2020, 20, 8584-8591.	9.1	19
6	Ferroelectric-Gated InSe Photodetectors with High On/Off Ratios and Photoresponsivity. <i>Nano Letters</i> , 2020, 20, 6666-6673.	9.1	53
7	Universal mechanical exfoliation of large-area 2D crystals. <i>Nature Communications</i> , 2020, 11, 2453.	12.8	394
8	Thickness-Controlled Synthesis of CoX ₂ (X = S, Se, and Te) Single Crystalline 2D Layers with Linear Magnetoresistance and High Conductivity. <i>Chemistry of Materials</i> , 2020, 32, 2321-2329.	6.7	35
9	InSe/hBN/graphite heterostructure for high-performance 2D electronics and flexible electronics. <i>Nano Research</i> , 2020, 13, 1127-1132.	10.4	48
10	Observation of the Kondo Effect in Multilayer Single-Crystalline VTe ₂ Nanoplates. <i>Nano Letters</i> , 2019, 19, 8572-8580.	9.1	52
11	Quasi-2D Transport and Weak Antilocalization Effect in Few-layered VSe ₂ . <i>Nano Letters</i> , 2019, 19, 4551-4559.	9.1	60
12	Epitaxy of Ultrathin SnSe Single Crystals on Polydimethylsiloxane: In-plane Electrical Anisotropy and Gate-tunable Thermopower. <i>Advanced Electronic Materials</i> , 2016, 2, 1600292.	5.1	31